

## General Description

The AOZ9530QV is an integrated half-bridge gate driver with smart functions. The device includes one half-bridge gate driver, capable of driving high-side and low-side N-channel MOSFETs. Using two AOZ9530QV for single phase motor driver and three AOZ9530QV for three phase motor drivers.

The device features multiple protection functions such as over current protection, short circuit protection, and over temperature protection. Moreover, AOZ9530QV provides adjustable gate drive sink and source current control. By doing this control, user can optimize performances of EMI and efficiency.

The AOZ9530QV is available in a 3mm×3mm QFN-18L package and is rated over a -40°C to +125°C ambient temperature range.

## Features

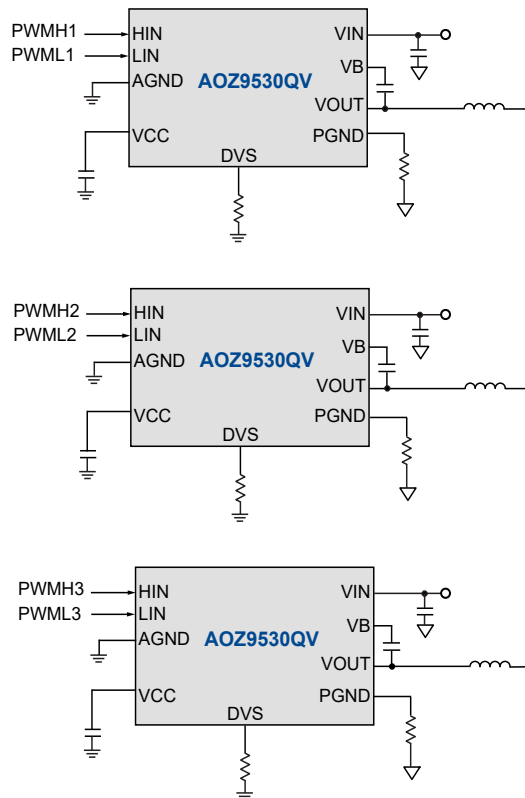
- Input voltage range:
  - 10.8V to 28 V
- Maximum Output Current 7A
- Adjustable Gate Drive Sink/Source Current
- Support 100% PWM Operation
- Integrated Bootstrap Diode
- Low  $R_{DS(ON)}$  internal NFETs
  - 11 mΩ for Both HS/LS
- Thermal Protection
- Over Current Protection
- Short Circuit Protection
- Thermally enhanced 18-pin 3×3 QFN

## Applications

- BLDC Motor Drive
- Fans and Pumps
- Power Tools



## Typical Application (Three Phases)



## Ordering Information

Part Number	Temperature Range	Package	Environmental
AOZ9530QV	-40 °C to +125 °C	QFN3x3-18L	Green



AOS products are offered in packages with Pb-free plating and compliant to RoHS standards. Please visit [www.aosmd.com/media/AOSGreenPolicy.pdf](http://www.aosmd.com/media/AOSGreenPolicy.pdf) for additional information.

## Pin Configuration

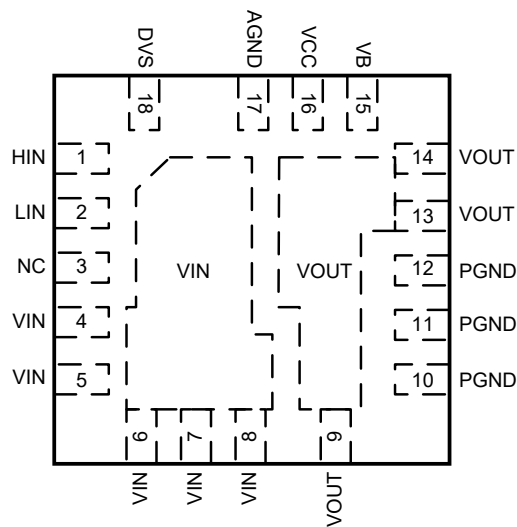


Figure 1. AOZ9530QV  
QFN3x3-18L

## Pin Description

Pin Number	Pin Name	Pin Function
1	HIN	PWM input for high-side MOSFET.
2	LIN	PWM input for low-side MOSFET.
3	NC	No connect.
4, 5, 6, 7, 8	VIN	Supply input. All VIN pins must be connected together.
9, 13, 14	VOUT	Motor drive output. All VOUT pins must be connected together.
10, 11, 12	PGND	Power ground.
15	VB	Bootstrap capacitor connection. Connect an external capacitor between VB and VOUT for supplying high-side MOSFET.
16	VCC	Supply input for analog functions. Bypass VCC to AGND with a 0.1 μF~10 μF ceramic capacitor and as close to VCC pin as possible.
17	AGND	Analog ground.
18	DVS	Adjustable gate drive source/sink current.

## Absolute Maximum Ratings

Exceeding the Absolute Maximum ratings may damage the device.

Parameter	Rating
VIN to AGND	-0.3V to 30V
VOUT to AGND	-0.3V to 30V
VOUT to AGND (Transient, 30 ns)	-7V to VIN + 7V
VB to AGND	-0.3V to 40V
DVS, VCC to AGND	-0.3V to 13.2V
HIN, LIN to AGND	-0.3V to 5.5V
PGND to AGND	-0.3V to +0.3V
PGND to AGND (Transient, 100 ns)	-6.5V to 6.5V
Junction Temperature (T <sub>J</sub> )	+150°C
Storage Temperature (T <sub>S</sub> )	-65°C to +150°C
ESD Rating	2kV

## Recommended Operating Conditions

The device is not guaranteed to operate beyond the Maximum Recommended Operating Conditions.

Parameter	Rating
Supply Voltage (V <sub>IN</sub> )	10V to 28V
Ambient Temperature (T <sub>A</sub> )	-40°C to +125°C
Package Thermal Resistance Θ <sub>JA</sub> Θ <sub>JC</sub>	40°C/W 6°C/W

## Electrical Characteristics

T<sub>A</sub> = 25°C, unless otherwise specified.

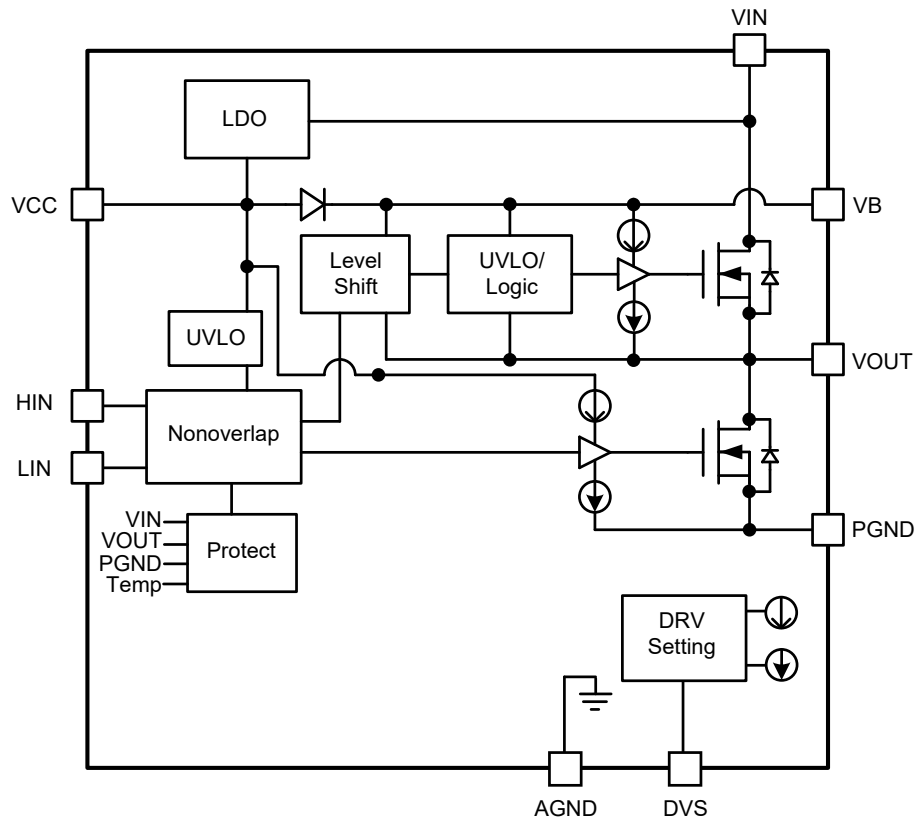
Symbol	Parameter	Conditions	Min	Typ	Max	Units
VCC	VCC	VIN = 12V, HIN/LIN=0V	7.4	8	8.6	V
	Line Regulation	VIN = 12V~24V, HIN/LIN=0V		0.1		%/V
I <sub>VCC_short</sub>	I <sub>VCC</sub> Short Current	VIN = 24V, HIN/LIN=0V, Monitor I <sub>VCC</sub>		1		mA
V <sub>UVLO_R</sub>	VCC UVLO Rising	VIN = 12V, VCC increase, Monitor DVS from low to high	6.9	7.5	8.1	V
V <sub>UVLO_F</sub>	VCC UVLO Falling	VIN = 12V, VCC decrease, Monitor DVS from high to low	4.7	5.1	5.6	V
V <sub>B_UVLO_R</sub>	VB-VOUT UVLO Rising	VIN = 20V, VB-VOUT increase, HIN = high, Monitor VOUT from low to high	5.8	7.2	8.4	V
V <sub>B_UVLO_F</sub>	VB-VOUT UVLO Falling	VIN = 20V, VB-VOUT decrease, HIN = high, Monitor VOUT from high to low	4.4	5.5	6.3	V
I <sub>VIN_ST</sub>	I <sub>VIN</sub> Standby Current	HIN/LIN=0V, Monitor VIN Current		1.5		mA
I <sub>VB-VOUT_ST</sub>	I <sub>VB-VOUT</sub> Standby Current	VIN = 10V, HIN/LIN=0V, VOUT=0V, VB-VOUT=8V, Monitor VB-VOUT Current		25		μA
V <sub>H_LIN_L</sub>	HIN/LIN Logic Low Voltage	VIN = 12V	0		1.2	V
V <sub>H_LIN_H</sub>	HIN/LIN Logic High Voltage	VIN = 12V	2.2		5.5	V
R <sub>H_LIN_IN</sub>	HIN/LIN Input Pull Low Impedance			280		kΩ
t <sub>HIN_RP</sub>	HIN Rising Propagation Delay	VIN = 10V, DVS = 20kΩ, VOUT to GND = 100Ω, HIN = low to high, Monitor HIN high TH to 10% VOUT		40		ns

## Electrical Characteristics

T<sub>A</sub> = 25 °C, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t <sub>HIN_FP</sub>	HIN Falling Propagation Delay	VIN = 10V, DVS = 20 kΩ, VOUT to GND = 100Ω, HIN = High to Low, Monitor HIN High TH to 90% VOUT		60		ns
t <sub>LIN_RP</sub>	LIN Rising Propagation Delay	VIN = 10V, DVS = 20 kΩ, VOUT to VIN = 100Ω, LIN = High to Low, Monitor LIN Low TH to 10% VOUT		70		ns
t <sub>LIN_FP</sub>	LIN Falling Propagation Delay	VIN = 10V, DVS = 20 kΩ, VOUT to VIN = 100Ω, LIN = Low to High, Monitor LIN High TH to 90% VOUT		40		ns
T <sub>DM_R</sub>	Delay Matching Rising	Difference between t <sub>HIN_RP</sub> , t <sub>LIN_RP</sub>		30		ns
T <sub>DM_F</sub>	Delay Matching Falling	Difference between t <sub>HIN_FP</sub> , t <sub>LIN_FP</sub>		20		ns
V <sub>DVS</sub>	DVS	VIN = 12V, DVS to GND = 20 kΩ		1		V
I <sub>DVS_MIN</sub>	DVS Min. Source Current	VIN = 12V, DVS = 4V		0.5		μA
I <sub>DVS_MAX</sub>	DVS Max. Source Current	VIN = 12V, DVS = 0.8V		140		μA
R <sub>H_ON</sub>	VIN-VOUT R <sub>ON</sub>	VIN = 12V, HIN = 5V, VB-VOUT = 8V, I <sub>VOUT</sub> = 1A		11		mΩ
R <sub>L_ON</sub>	VOUT-PGND R <sub>ON</sub>	VIN = 12V, LIN = 5V, PGND = 0, I <sub>VOUT</sub> = 1A		11		mΩ
V <sub>SD</sub>	Boost Diode Forward Voltage	Forward Current = 2 mA		0.15		V
T <sub>OTP</sub>	Over Temperature Protection	VIN = 12V		140		°C
I <sub>OCP</sub>	Over Current Protection	VIN = 12V		14		A
I <sub>SCP</sub>	Short Current Protection	VIN = 12V		28		A
t <sub>OC</sub>	OCP/SCP Deglitch Time	VIN = 12V		1.5		μs

### Functional Block Diagram



## Typical Characteristics

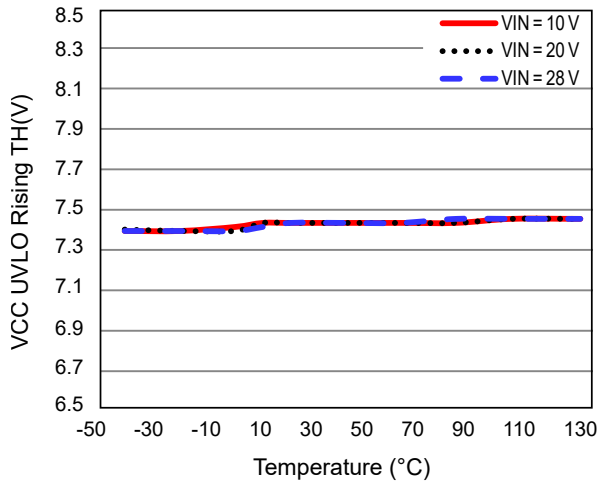


Figure 2. VCC UVLO Rising Threshold

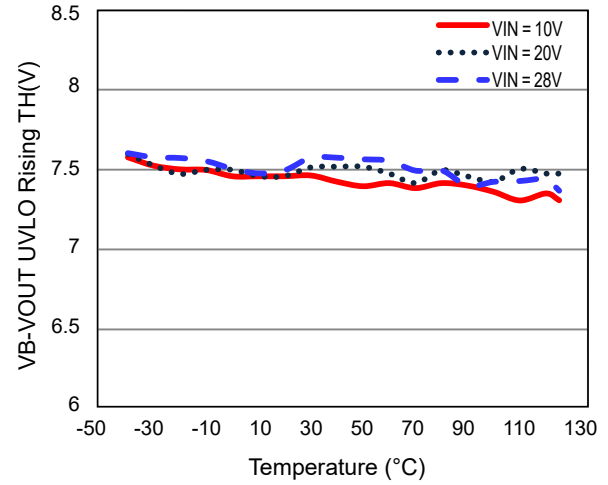


Figure 3. VB-VOUT UVLO Rising Threshold

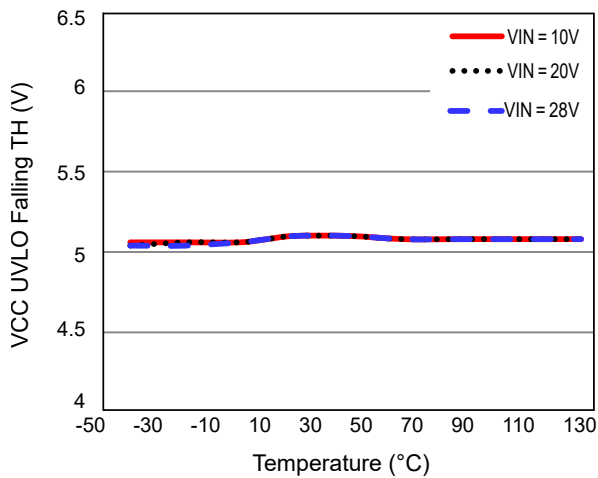


Figure 4. VCC UVLO Falling Threshold

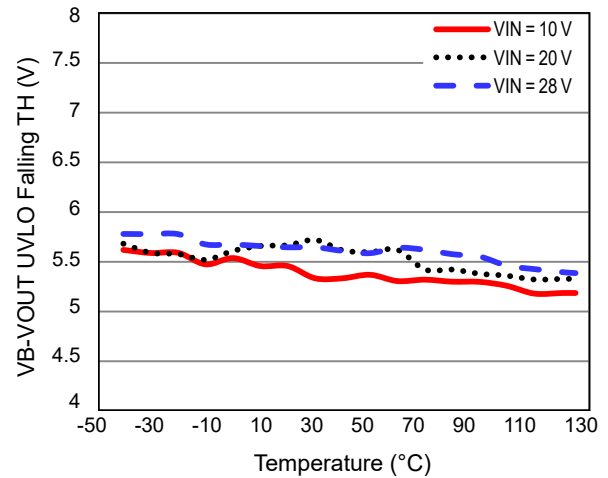


Figure 5. VB-VOUT UVLO Falling Threshold

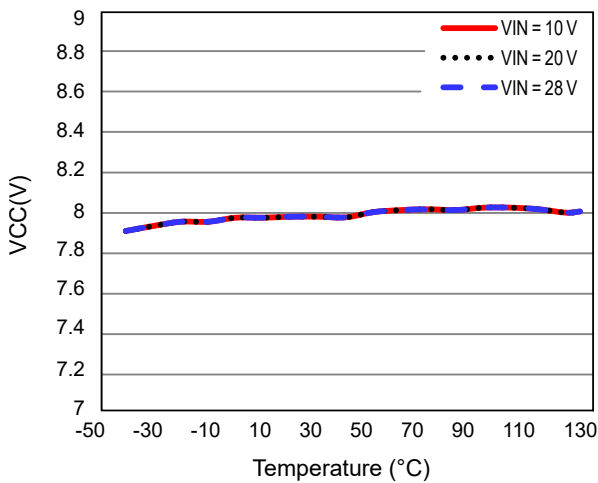


Figure 6. VCC Regulation

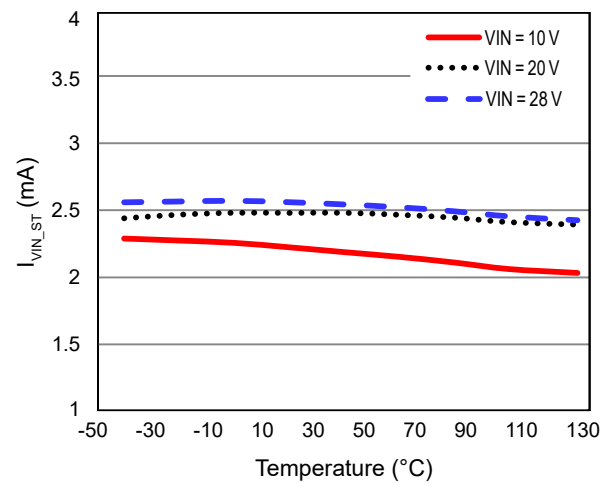


Figure 7. Input Standby Current

Typical Characteristics (Continued)

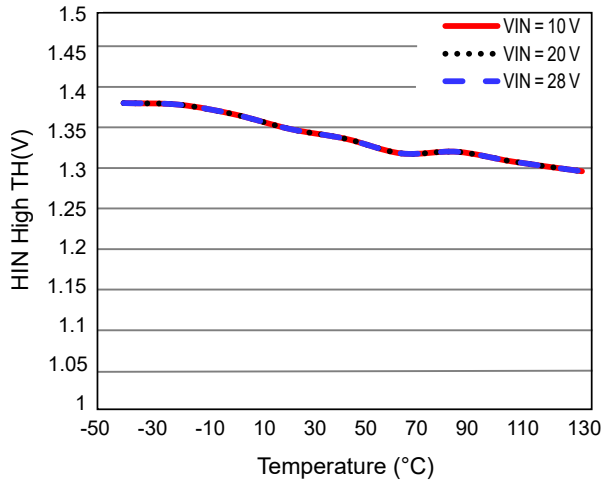


Figure 8. HIN High Threshold

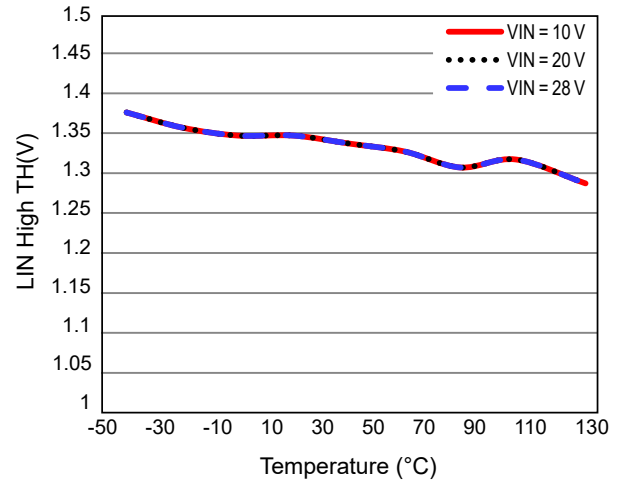


Figure 9. LIN High Threshold

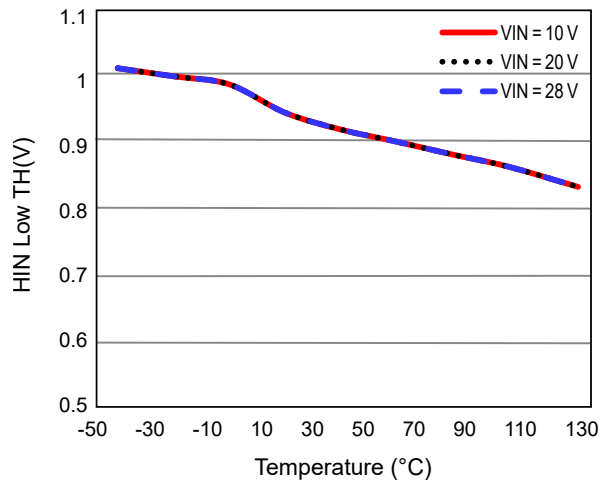


Figure 10. HIN Low Threshold

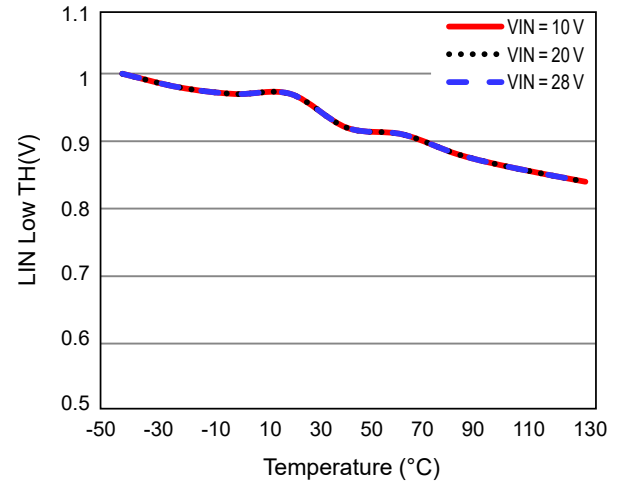


Figure 11. LIN Low Threshold

## Detailed Description

The AOZ9530QV is an integrated half-bridge gate driver for motor drive applications. The device includes one half-bridge gate driver, capable of driving high-side and low-side N-channel MOSFETs. The AOZ9530QV provides adjustable source/sink current of both high/low-side gate drive output current which can optimize performances of EMI and efficiency on different PCB layout and applications.

In addition, the AOZ9530QV provides several fault protections, such as OCP, UVLO, SCP, OTP and non-overlapping mechanism.

The AOZ9530QV is available in 18-pin 3mm×3mm QFN package.

### Input Power Architecture

The AOZ9530QV integrates an internal linear regulator to generate 8V (±3%) VCC from input pins. If input voltage is lower than 5.1V, the linear regulator will be triggered VB-VOUT UVLO. The VCC maximum source current is 1mA. Therefore, extra external source is needed when operation switching frequency exceeds 30kHz.

### Non-overlapping

For forbidding shoot-through, HIN or LIN is invalid when HIN or LIN goes high state before other one. For example, low-side gate state keeps low regardless of the state of LIN when HIN is high at first, and vice versa.

So when shoot-through occurs, VOUT will follow the previous normal state, as illustrated Figure 12.

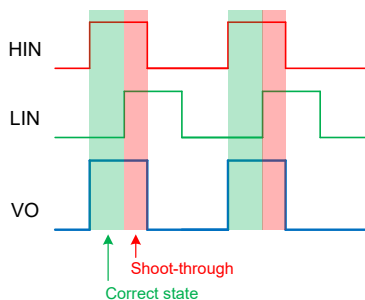


Figure 12. Shoot-through Behavior

## Fault Protection

### Over Current Protection (OCP)

There are fixed OCP/SCP points on AOZ9530QV  $I_{OCP} = 14A$  and  $I_{SCP} = 28A$ .

The time point of OCP detection is 1  $\mu s$  (debounce time) after the rising edge of HIN. If the current exceeds the  $I_{OCP}$ , the internal counter will start counting, as illustrated Figure 13. When 14 consecutive OCPs are detected, the high side

MOSFET will be turned off on the 14th time and the low side MOSFET is turned on. This behavior is called current limit. When the current is less than  $0.8 * I_{OCP}$ , the current limit is released.

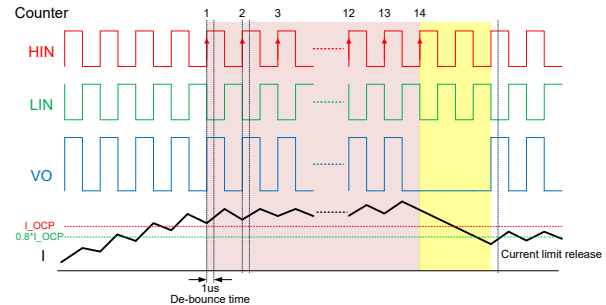


Figure 13. OCP timing diagram

### Short Current Protection (SCP)

If the current is greater than SCP point, AOZ9530QV enters SCP, VTP pin will be pulled high, and then AOZ9530QV enters latch, VCC needs to be reset to return to normal operation state.

### Over Temperature Protection (OTP)

When the junction temperature reach 140°C, AOZ9530QV enters OTP, and release when the temperature drops to 120°C.

### Adjustable Source/Sink Current

It's hard to meet all of EMI specifications in different applications. So, AOZ9530QV provides external adjustable resistors for tuning gate drive source and sink current.

DVS is used to tune gate drive source and sink current, respectively. A resistor connects between DVS pin and GND to setting gate drive source/sink current by internal current mirror, as illustrated Figure 14. Source and sink current use maximum capability to drive when DVS pin is floating or the voltage on DVS pin exceed 4V. The suggestion range of  $R_{DVS}$  is 20 k $\Omega$ ~100 k $\Omega$ .

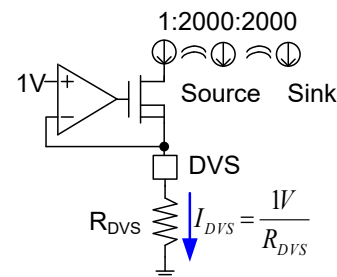


Figure 14. Source/Sink Current Setting



In addition, source and sink current controls are implemented only during MOSFET Miller effect and  $V_{GS} > 1V$ , as illustrated Figure 15.

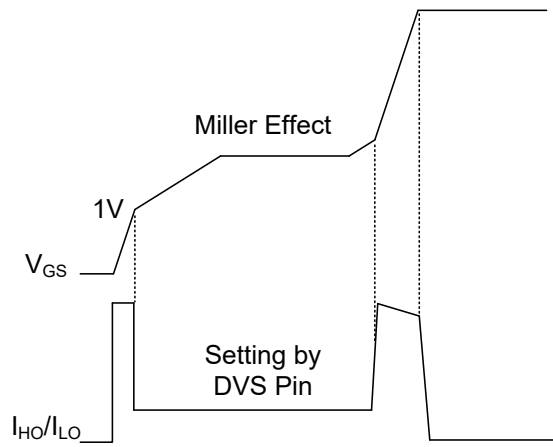
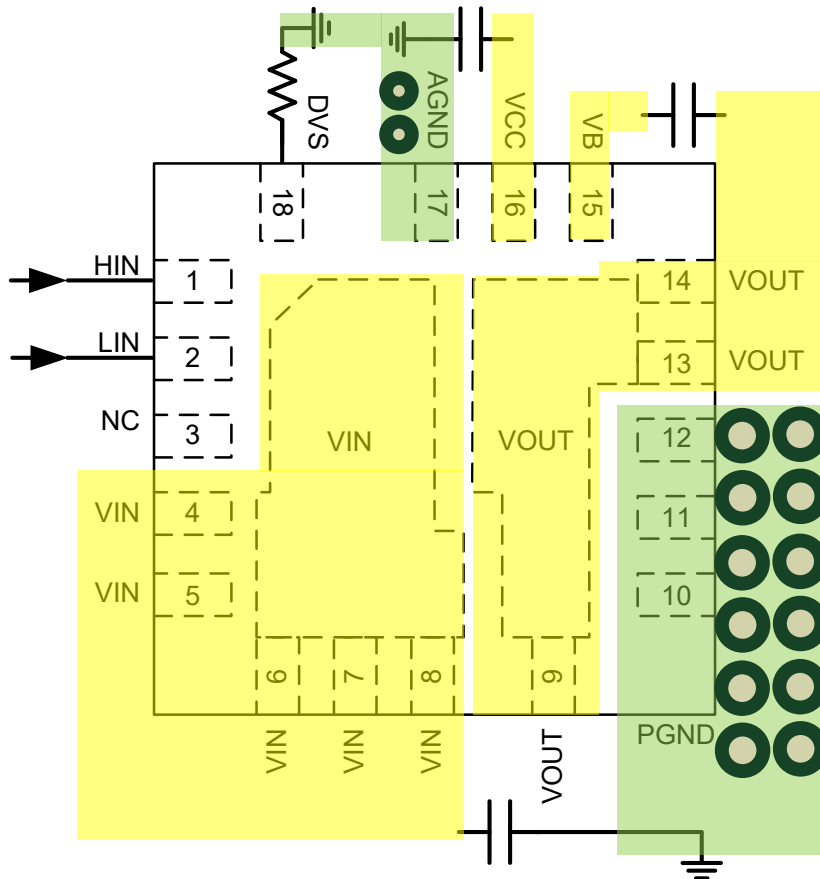


Figure 15. Source/Sink Current Implement Waveform

### Layout Considerations

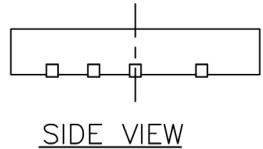
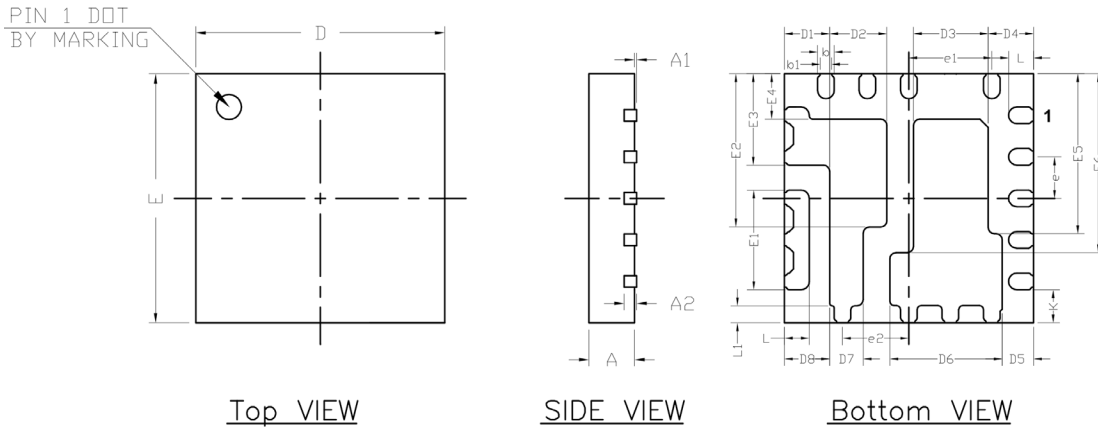
Several layout tips are listed below for the best electric and thermal performance.

1. The VIN pins and pad are connected to internal high side switch drain. They are also low resistance thermal conduction path. Connected a large copper plane to VIN pins to help thermal dissipation.
2. Input capacitors should be connected to the VIN pins and the PGND pins as close as possible to reduce the switching spikes.
3. The VOUT pins and pad are connected to internal low side switch drain. They are low resistance thermal conduction path and most noisy switching node. Connected a large copper plane to VOUT pins to help thermal dissipation.
4. Decoupling capacitor  $C_{VCC}$  should be connected to VCC and AGND as close as possible.
5. Bootstrap capacitor  $C_B$  should be connected to VB and VOUT as close as possible.
6. A ground plane is preferred. PGND and AGND must be connected to the ground plane through vias.
7. Keep sensitive signal traces such as feedback trace and digital signals far away from the VOUT pins.

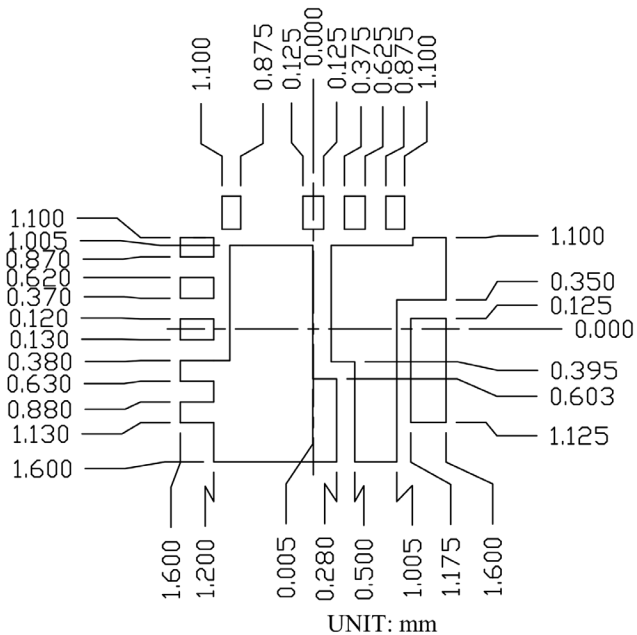


Package Dimensions, QFN3x3-18L

QFN3x3\_18L\_EP2\_S PACKAGE OUTLINE



RECOMMENDED LAND PATTERN

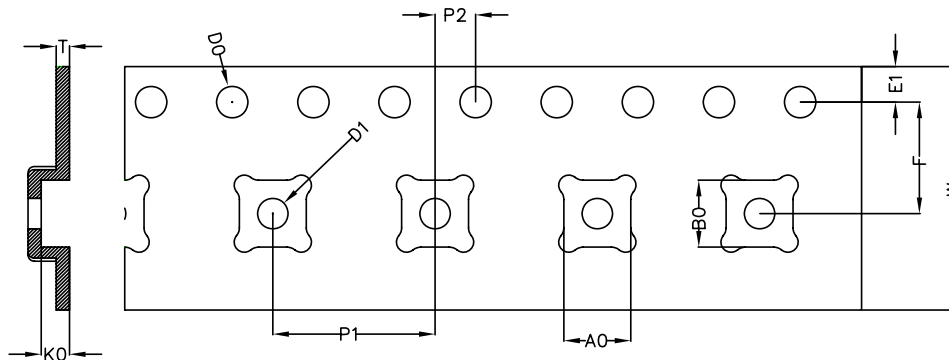


SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.55	0.65	0.018	0.022	0.026
A1	0.00	-	0.05	0.000	-	0.002
A2	0.10	0.15	0.20	0.004	0.006	0.008
E	2.90	3.00	3.10	0.114	0.118	0.122
E1	1.15	1.20	1.25	0.045	0.047	0.049
E2	1.80	1.85	1.90	0.071	0.073	0.075
E3	1.00	1.10	1.20	0.039	0.043	0.047
E4	0.45	0.55	0.65	0.018	0.021	0.025
E5	1.88	1.93	1.98	0.074	0.076	0.078
E6	2.10	2.15	2.20	0.083	0.085	0.087
D	2.90	3.00	3.10	0.114	0.118	0.122
D1	0.45	0.55	0.65	0.018	0.021	0.025
D2	0.64	0.69	0.74	0.025	0.027	0.029
D3	0.85	0.90	0.95	0.033	0.035	0.037
D4	0.45	0.55	0.65	0.018	0.021	0.025
D5	0.33	0.38	0.43	0.013	0.015	0.017
D6	1.30	1.35	1.40	0.051	0.053	0.055
D7	0.35	0.40	0.45	0.014	0.016	0.018
D8	0.50	0.55	0.60	0.019	0.021	0.023
L	0.25	0.30	0.35	0.010	0.012	0.014
L1	0.15	0.20	0.25	0.006	0.008	0.010
b	0.15	0.20	0.25	0.006	0.008	0.010
b1	0.09	0.14	0.19	0.004	0.006	0.007
K	0.35	0.40	0.45	0.014	0.016	0.018
e	0.50			0.020		
e1	1.00			0.039		
e2	0.80			0.031		

NOTE  
CONTROLLING DIMENSION IS MILLIMETER.

## Tape and Reel Dimensions, QFN3x3-18L

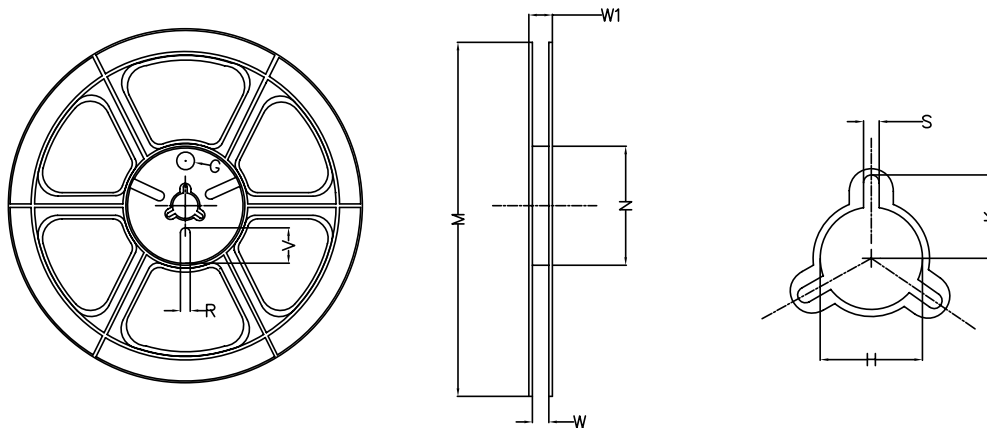
### QFN3x3 18L EP2 S Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	W	E1	F	P0	P1	P2	T
QFN3X3_18L	3.30 ±0.10	3.30 ±0.10	0.80 ±0.10	1.55 ±0.05	1.50 Min.	12.00 +0.30 -0.00	1.75 ±0.10	5.50 ±0.10	4.00 ±0.10	8.00 ±0.10	2.00 ±0.10	0.30 ±0.05

### QFN3x3 18L EP2 S Reel



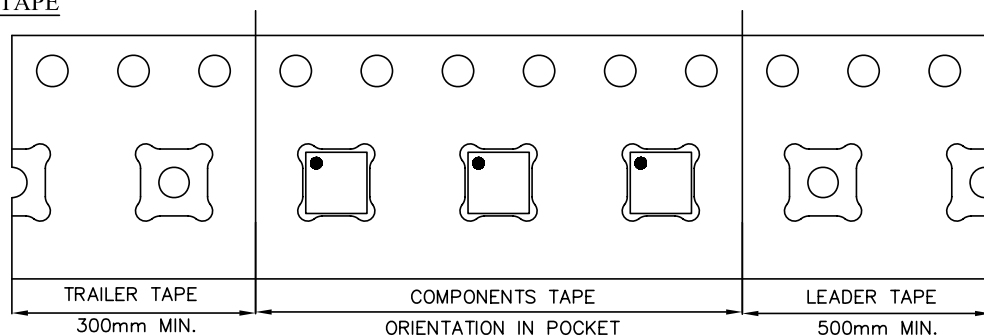
UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	S	K	G	R	V
12 mm	ø330	ø330.00 ±2.00	ø101.6 ±2.00	12.40 +2.00 -0.00	12.40 +3.00 -0.20	ø13.20 ±0.30	1.70-2.60	---	---	---	---

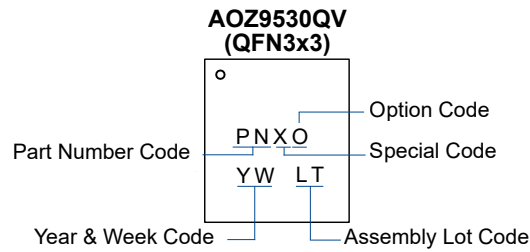
### QFN3x3 18L EP2 S TAPE

Leader / Trailer  
& Orientation

Unit Per Reel:  
5000pcs



## Part Marking



Part Number	Description	Code
AOZ9530QV	Green Product	AF00

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- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.